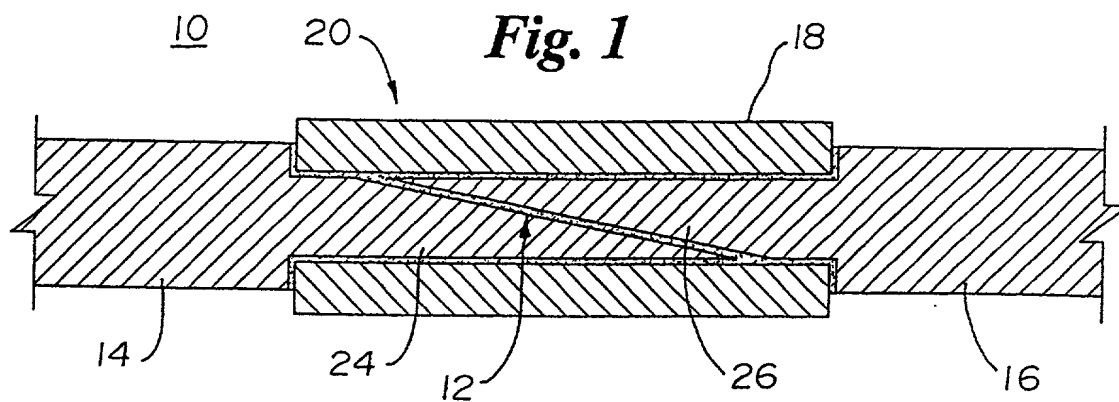
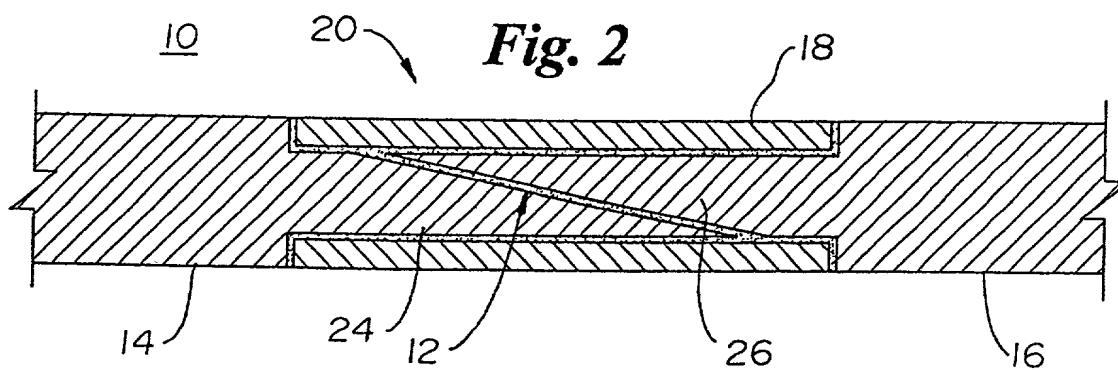


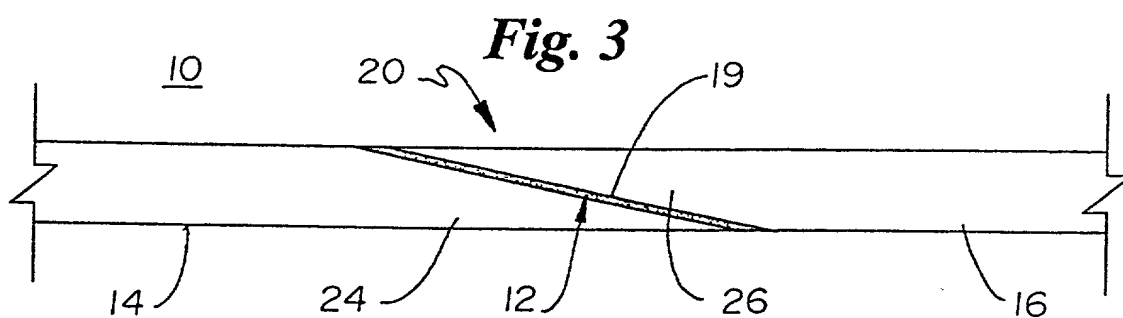
10 **Fig. 1**



10 **Fig. 2**



10 **Fig. 3**



10 **Fig. 4**

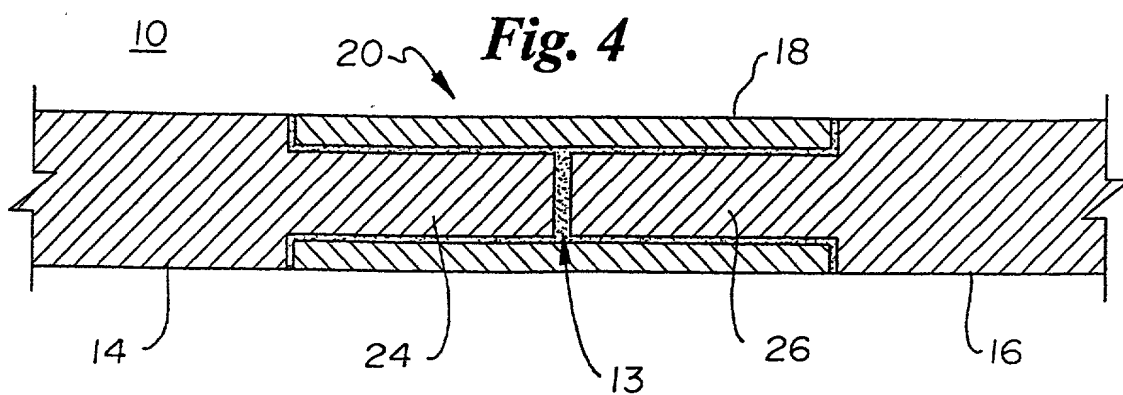


Fig. 5

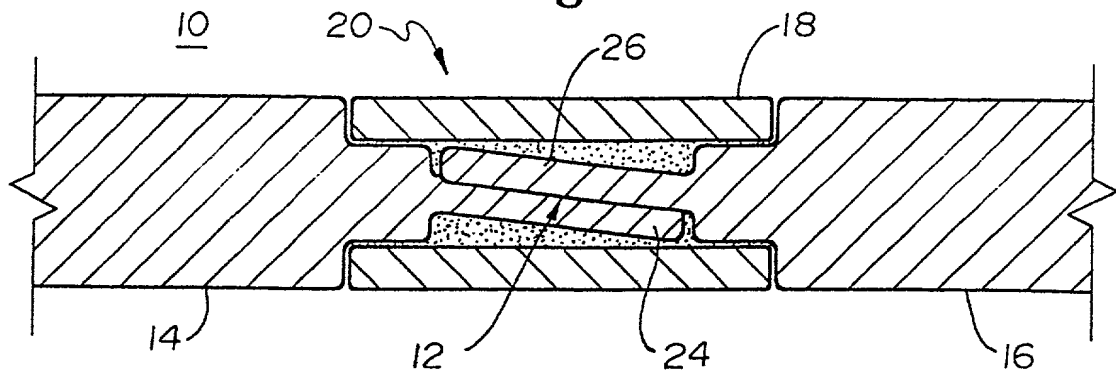


Fig. 6A

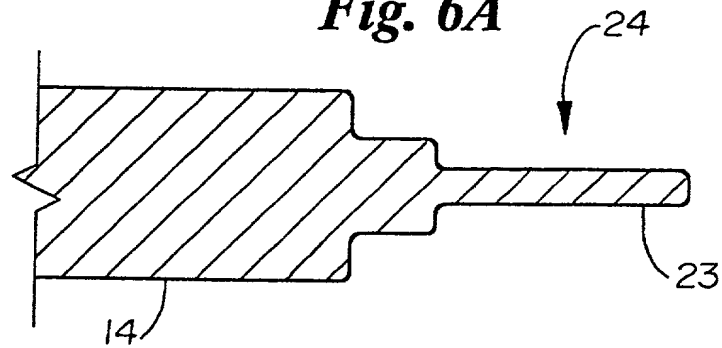


Fig. 6B

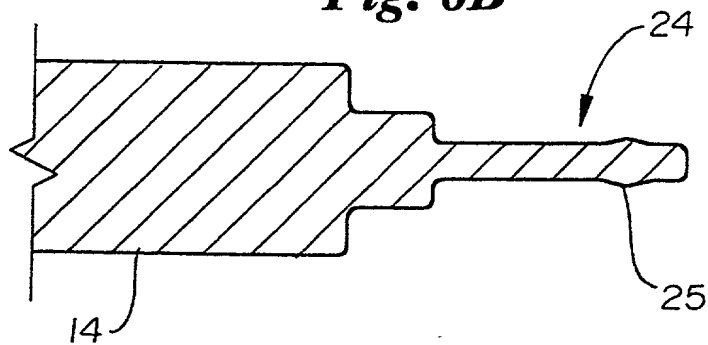
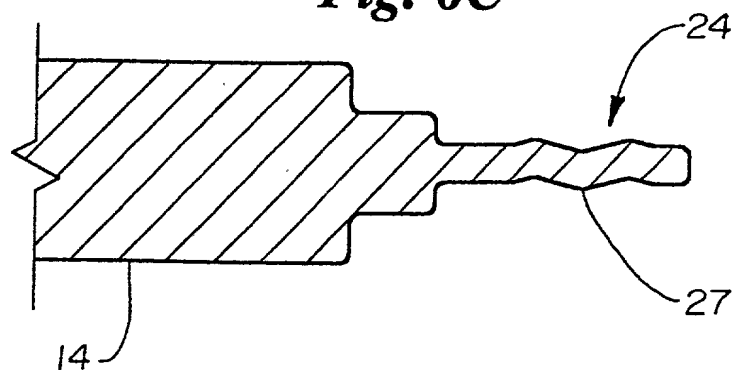
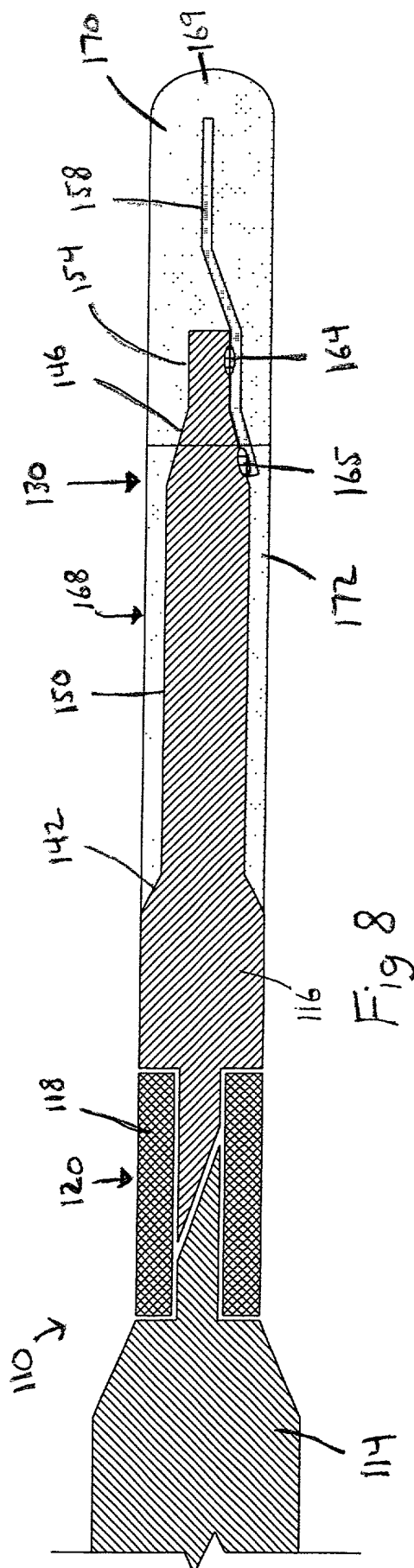
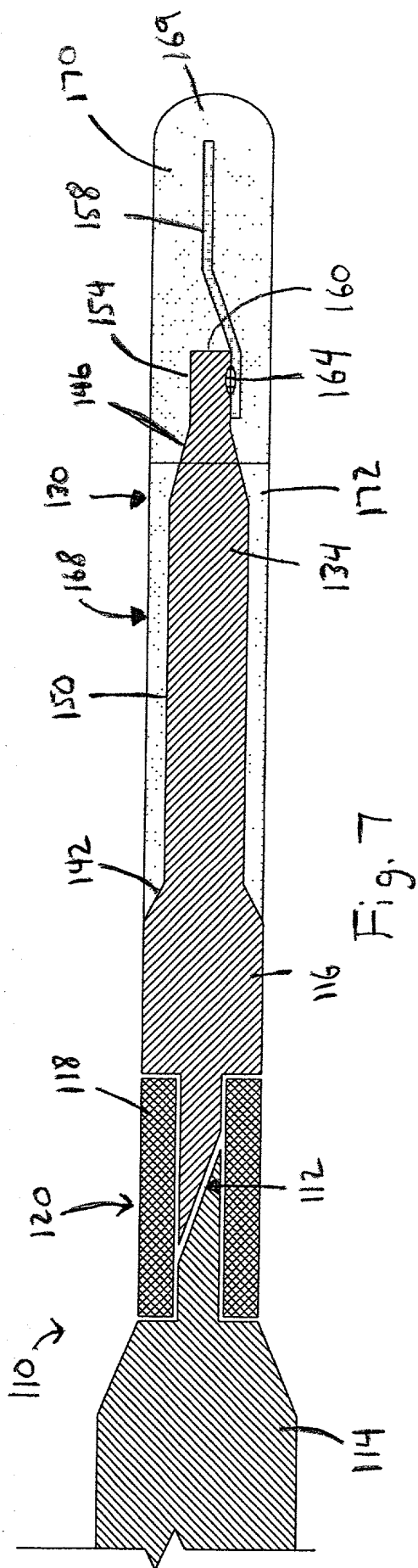
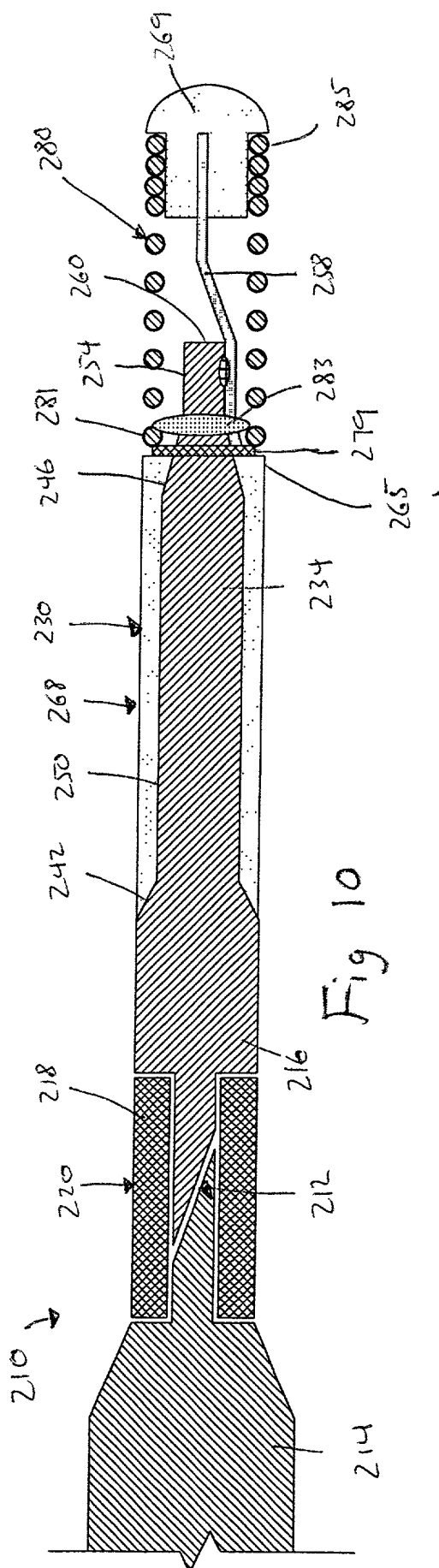
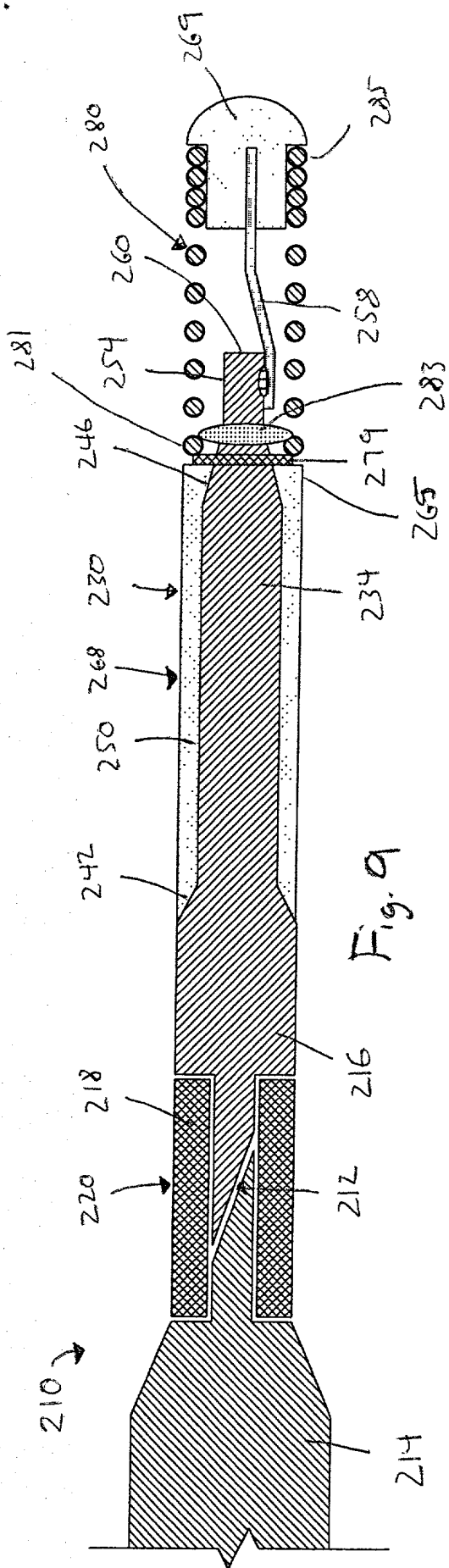
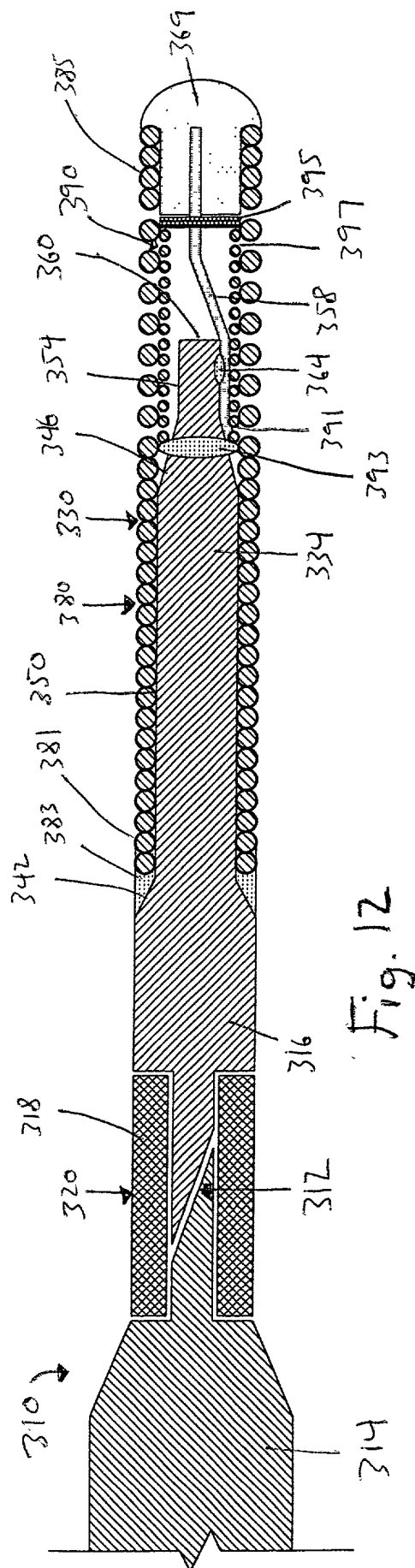
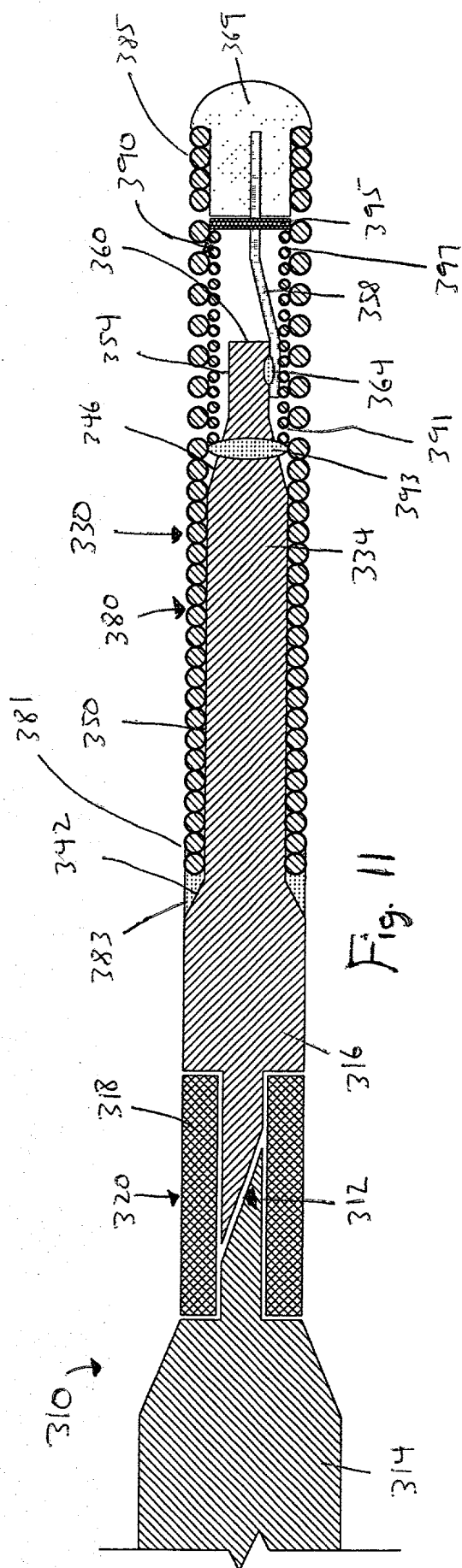


Fig. 6C









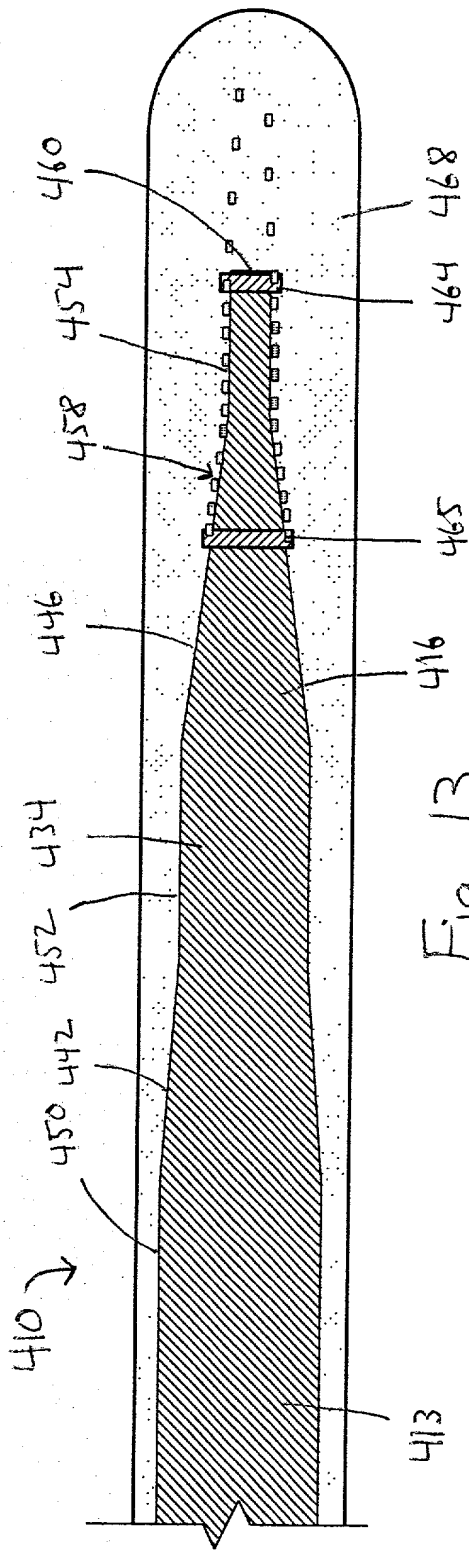


Fig. 13

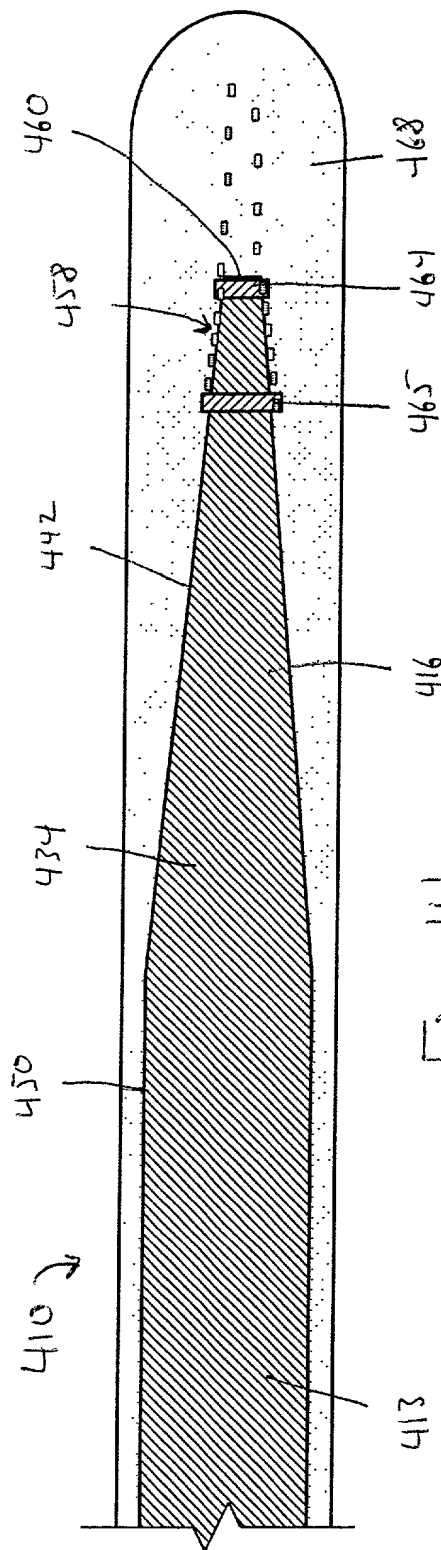


Fig. 14

FIG. 15 is a cross-sectional view of a device 410 in a first state. The device 410 includes a substrate 413, a layer 450, a layer 434, a layer 442, and a layer 468. A layer 465 is disposed between the layer 442 and the layer 468. A layer 454 is disposed between the layer 450 and the layer 434. A layer 458 is disposed between the layer 434 and the layer 442. A layer 464 is disposed between the layer 465 and the layer 468. A layer 454 is disposed between the layer 450 and the layer 434. A layer 458 is disposed between the layer 434 and the layer 442. A layer 464 is disposed between the layer 465 and the layer 468.

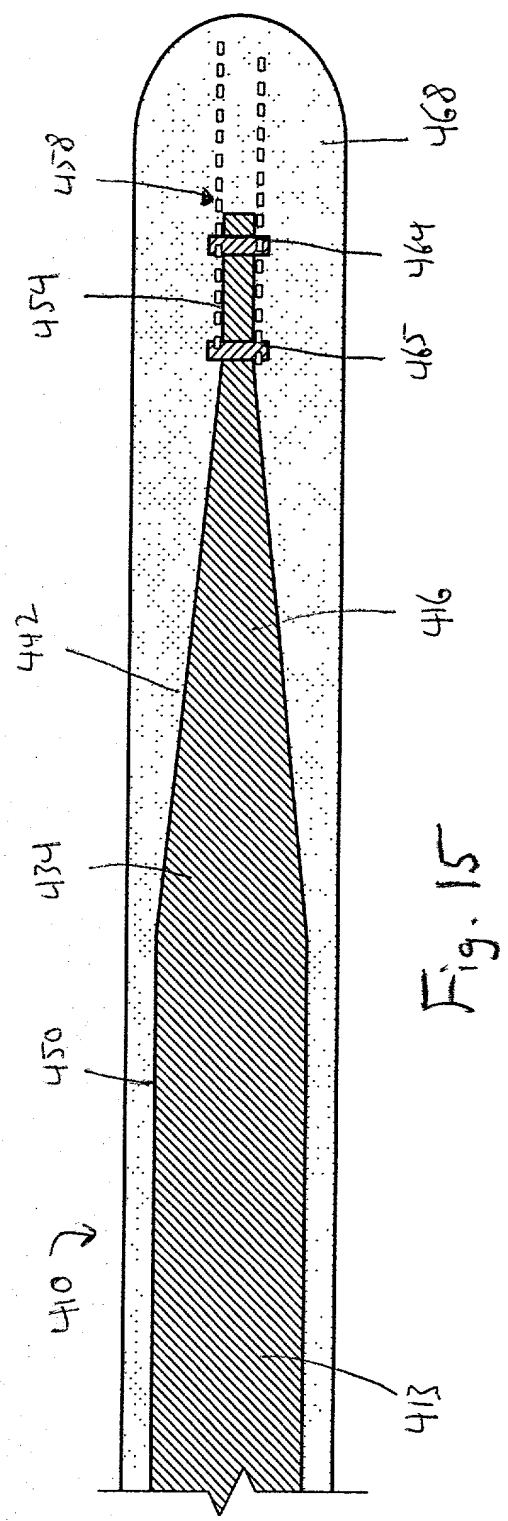


Fig. 15

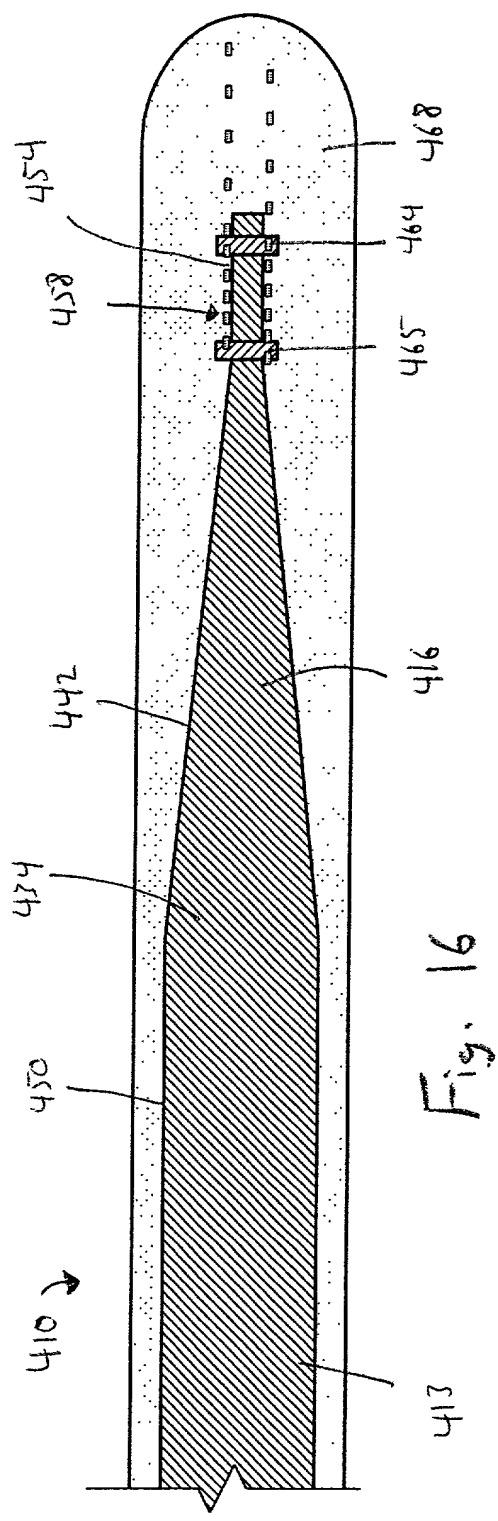


Fig. 16

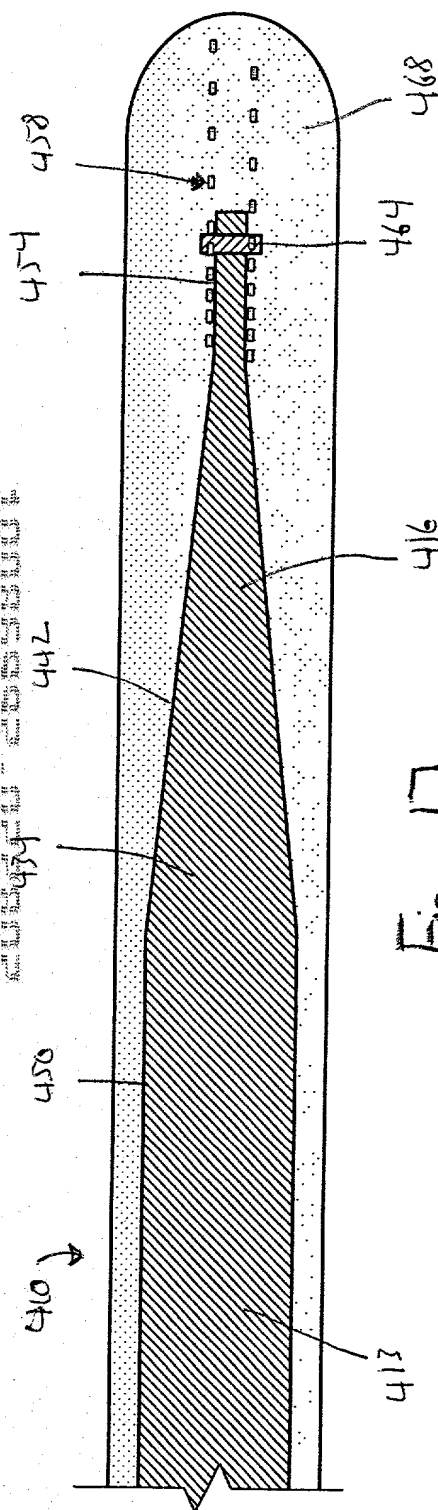


Fig. 17

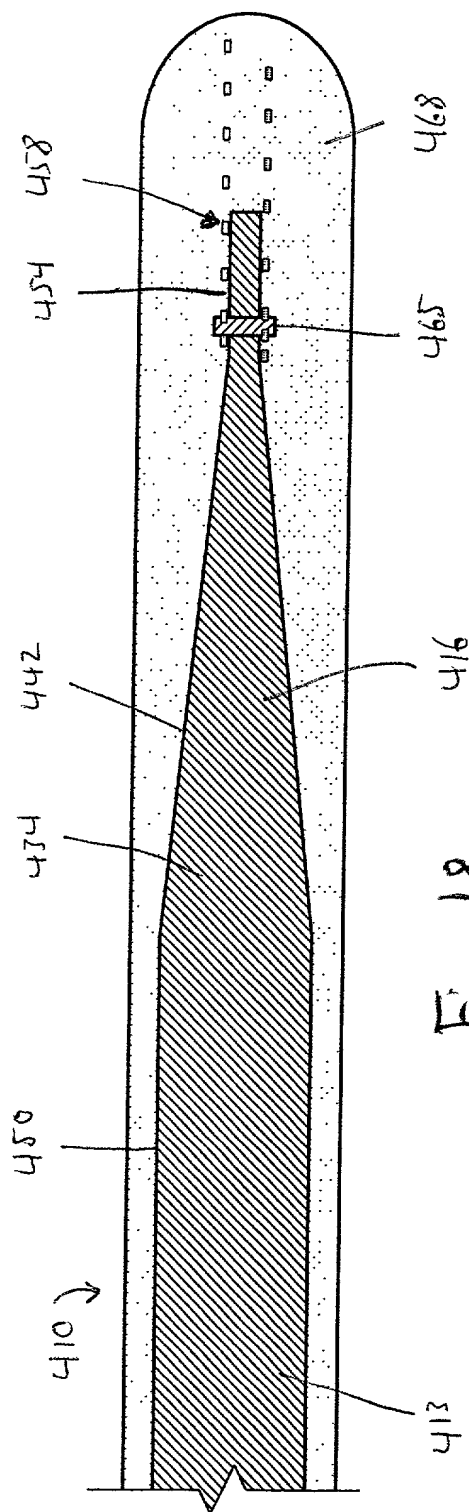


Fig. 18

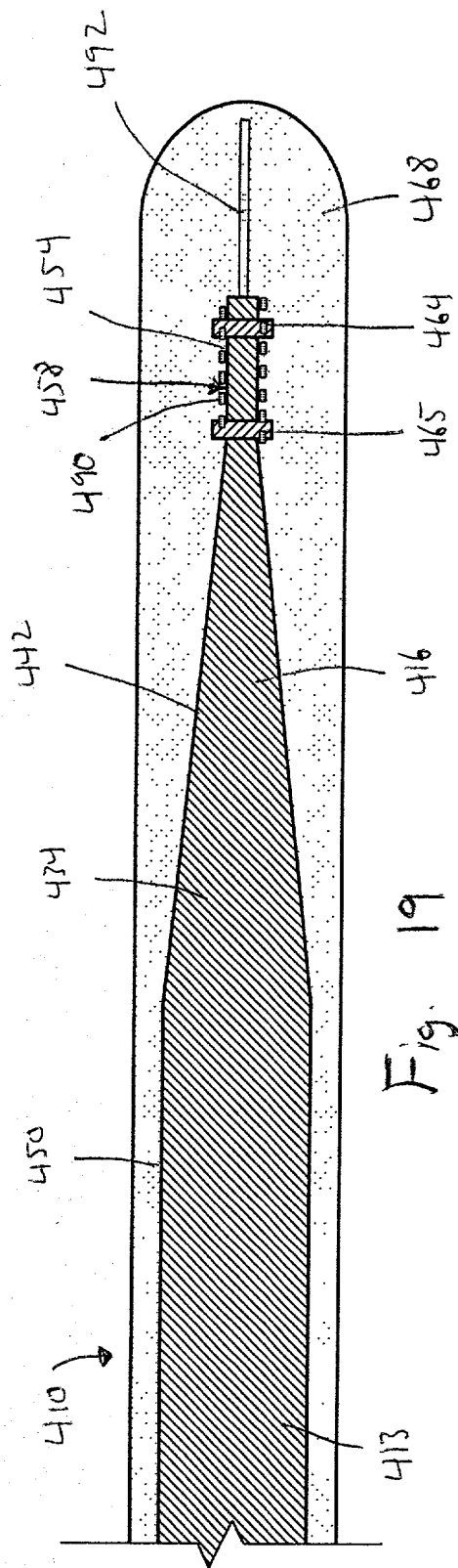


Fig. 19

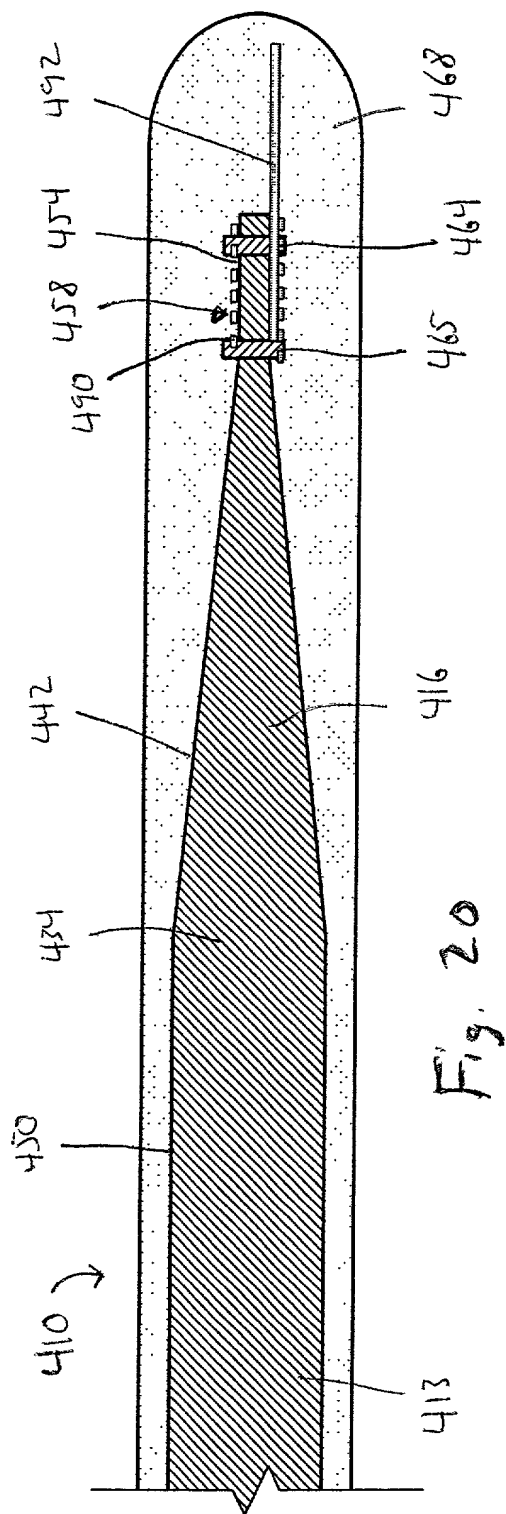
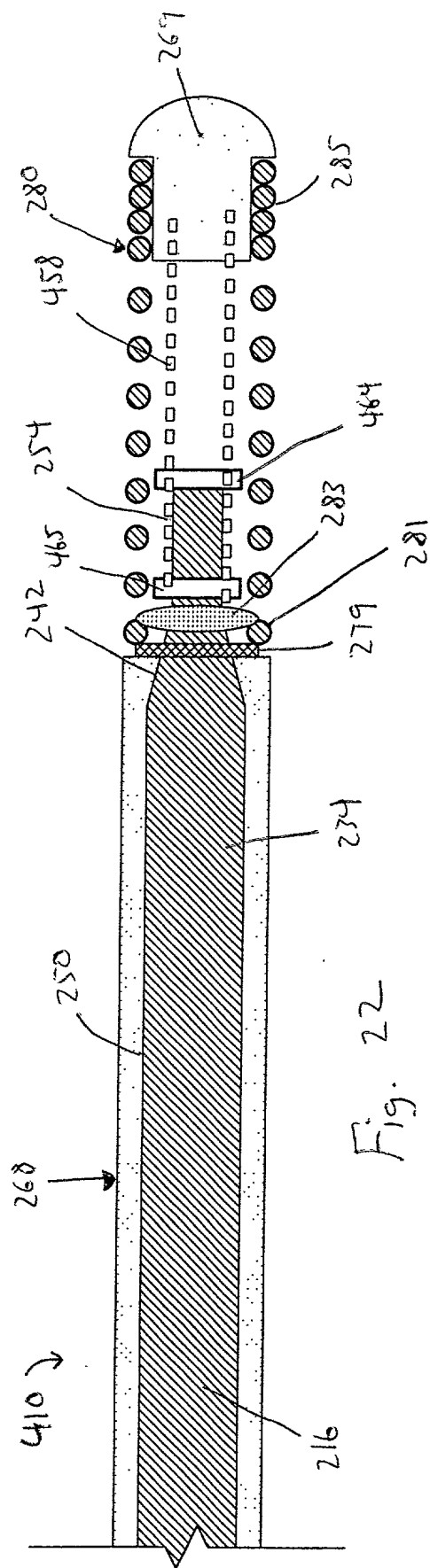
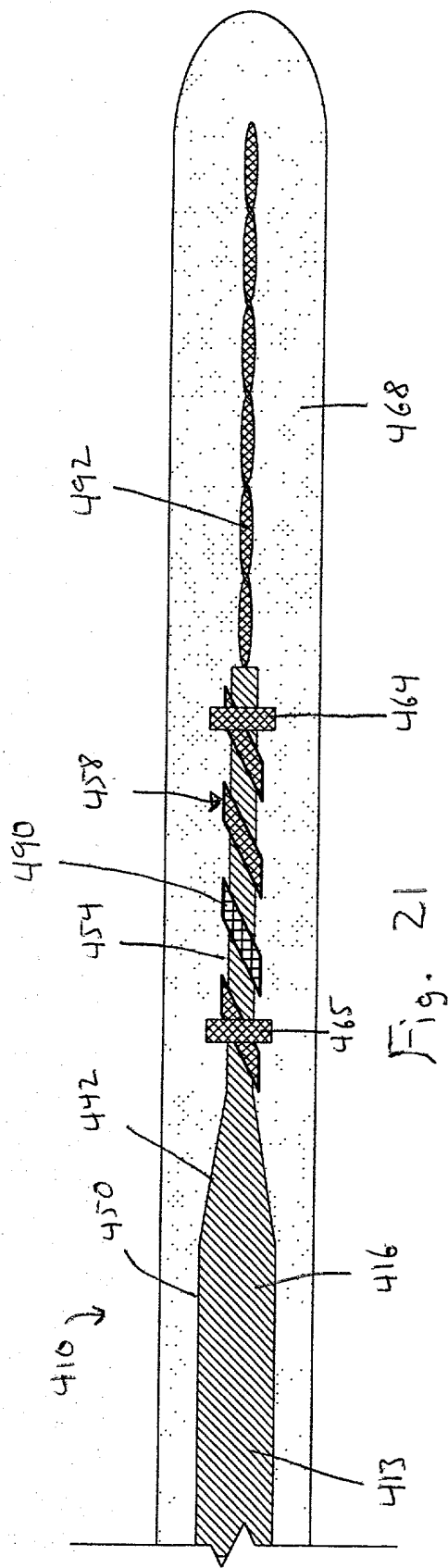


Fig. 20



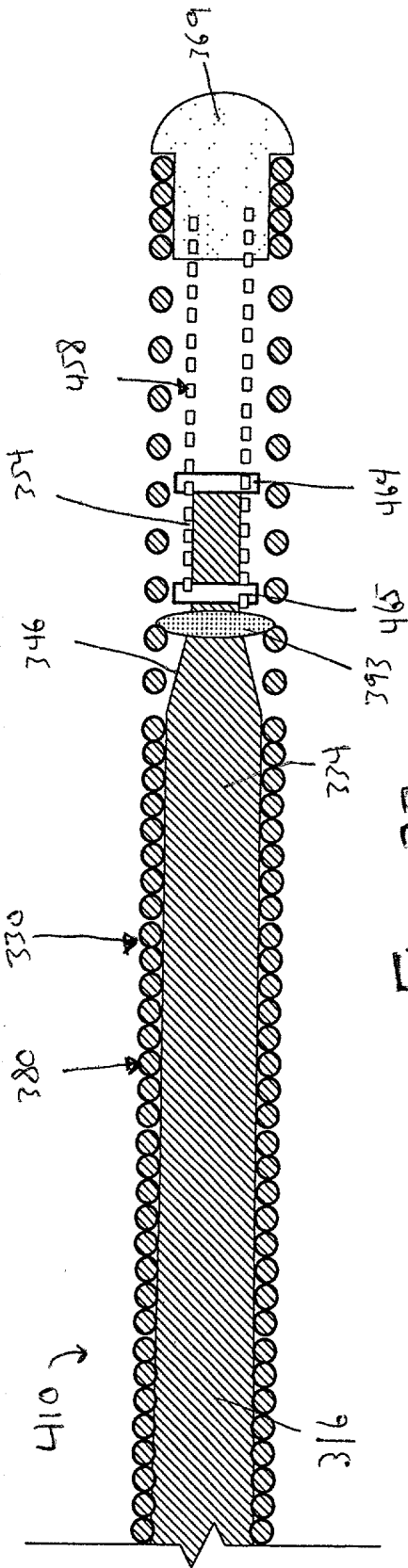


Fig. 23